

# IRFF210, IRFF211, IRFF212, IRFF213

1.8A, and 2.2A, 150V and 200V, 1.5 and 2.4 Ohm,  
N-Channel Power MOSFETs

January 1998

## Features

- 1.8A and 2.2A, 150V to 200V
- $r_{DS(ON)} = 1.5\Omega$  and  $2.4\Omega$
- Single Pulse Avalanche Energy Rated
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Related Literature
  - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

## Ordering Information

PART NUMBER	PACKAGE	BRAND
IRFF210	TO-205AF	IRFF210
IRFF211	TO-205AF	IRFF211
IRFF212	TO-205AF	IRFF212
IRFF213	TO-205AF	IRFF213

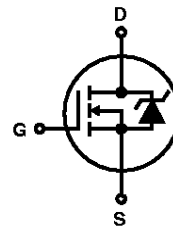
NOTE: When ordering, include the entire part number.

## Description

These are N-Channel enhancement mode silicon gate power field effect transistors. They are advanced power MOSFETs designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. All of these power MOSFETs are designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

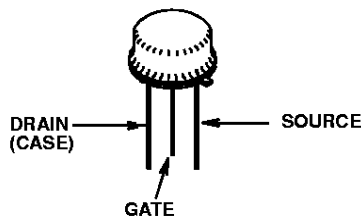
Formerly developmental type TA17442.

## Symbol



## Packaging

JEDEC TO-205AF



## IRFF210, IRFF211, IRFF212, IRFF213

### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

	IRFF210	IRFF211	IRFF212	IRFF213	UNITS
Drain to Source Voltage (Note 1) . . . . . $V_{DS}$	200	150	200	150	V
Drain to Gate Voltage ( $R_{GS} = 20k\Omega$ ) (Note 1) . . . . . $V_{DGR}$	200	150	200	150	V
Continuous Drain Current . . . . . $I_D$	2.2	2.2	1.8	1.8	A
Pulsed Drain Current (Note 3) . . . . . $I_{DM}$	9.0	9.0	7.5	7.5	A
Gate to Source Voltage . . . . . $V_{GS}$	$\pm 20$	$\pm 20$	$\pm 20$	$\pm 20$	V
Maximum Power Dissipation . . . . . $P_D$	15	15	15	15	W
Linear Derating Factor . . . . .	0.12	0.12	0.12	0.12	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy Rating (Note 4) . . . . . $E_{AS}$	30	30	30	30	mJ
Operating and Storage Temperature . . . . . $T_J, T_{STG}$	-55 to 150	-55 to 150	-55 to 150	-55 to 150	$^\circ\text{C}$
Maximum Temperature for Soldering					
Leads at 0.063in (1.6mm) from Case for 10s . . . . . $T_L$	300	300	300	300	$^\circ\text{C}$
Package Body for 10s, See Techbrief 334 . . . . . $T_{pk}$	260	260	260	260	$^\circ\text{C}$

**CAUTION:** Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

**NOTE:**

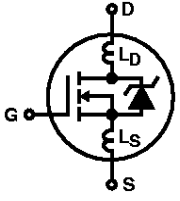
- $T_J = 25^\circ\text{C}$  to  $125^\circ\text{C}$ .

### Electrical Specifications $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

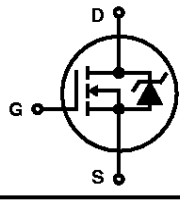
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage IRFF210, IRFF212	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$ (Figure 10)	200	-	-	V
			IRFF211, IRFF213	150	-	-
Gate to Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2.0	-	4.0	V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = \text{Rated } BV_{DSS}, V_{GS} = 0V$ $V_{DS} = 0.8 \times \text{Rated } BV_{DSS}, V_{GS} = 0V, T_J = 125^\circ\text{C}$	-	-	25	$\mu A$
			-	-	250	$\mu A$
On-State Drain Current (Note 2) IRFF210, IRFF211	$I_{D(ON)}$	$V_{DS} > I_{D(ON)} \times r_{DS(ON)MAX}, V_{GS} = 10V$ (Figure 7)	2.2	-	-	A
			IRFF212, IRFF213	1.8	-	-
Gate to Source Leakage Forward	$I_{GSS}$	$V_{GS} = \pm 20V$	-	-	$\pm 100$	nA
Drain to Source On Resistance (Note 2) IRFF210, IRFF211	$r_{DS(ON)}$	$V_{GS} = 10V, I_D = 1.25A$ (Figures 8, 9)	-	1.0	1.5	$\Omega$
			IRFF212, IRFF213	-	1.5	2.4
Forward Transconductance (Note 2)	$g_{fs}$	$V_{GS} > I_{D(ON)} r_{DS(ON)MAX}, I_D = 1.25A$ (Figure 12)	0.8	1.3	-	S
Turn-On Delay Time	$t_{d(ON)}$	$I_D \approx 2.2A, R_G = 9.1\Omega, V_{GS} = 10V,$ $V_{DD} \approx 0.5BV_{DSS}$ (Figures 15, 16) MOSFET Switching Times are Essentially Independent of Operating Temperature $R_L = 33\Omega$ for $V_{DS} = 75V$ $R_L = 44\Omega$ for $V_{DS} = 100V$	-	8	15	ns
Rise Time	$t_r$		-	15	25	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	10	15	ns
Fall Time	$t_f$		-	8	15	ns
Total Gate Charge (Gate to Source + Gate to Drain)	$Q_g(TOT)$		$V_{GS} = 10V, I_D = 2.2A, V_{DS} = 0.8 \times \text{Rated } BV_{DSS}, I_{G(REF)} = 1.5mA.$ (Figures 14, 19, 20) Gate Charge is Essentially Independent of Operating Temperature	-	5.0	7.5
Gate to Source Charge	$Q_{gs}$	-		2.0	-	nC
Gate to Drain "Miller" Charge	$Q_{gd}$	-		3.0	-	nC
Input Capacitance	$C_{ISS}$	$V_{GS} = 0V, V_{DS} = 25V, f = 1.0MHz$ (Figure 11)	-	135	-	pF
Output Capacitance	$C_{OSS}$		-	60	-	pF
Reverse to Transfer Capacitance	$C_{RSS}$		-	16	-	pF

## IRFF210, IRFF211, IRFF212, IRFF213

### Electrical Specifications $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Internal Drain Inductance	$L_D$	Measured from the Drain Lead, 5mm (0.2in) from Header to Center of Die	Modified MOSFET Symbol Showing the Internal Device Inductances 	-	5.0	-	nH
Internal Source Inductance	$L_S$	Measured from the Source Lead, 5mm (0.2in) from Header to Source Bonding Pad		-	15	-	nH
Junction to Case	$R_{\theta JC}$			-	-	8.33	$^\circ\text{C/W}$
Junction to Ambient	$R_{\theta JA}$	Free Air Operation		-	-	175	$^\circ\text{C/W}$

### Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Continuous Source to Drain Current	$I_{SD}$	Modified MOSFET Symbol Showing the Integral Reverse P-N Junction Rectifier 		-	-	2.2	A
Pulse Source to Drain Current (Note 3)	$I_{SDM}$			-	-	9.0	A
Source to Drain Diode Voltage (Note 2)	$V_{SD}$	$T_J = 25^\circ\text{C}$ , $I_{SD} = 2.2\text{A}$ , $V_{GS} = 0\text{V}$ (Figure 13)		-	-	2.0	V
Reverse Recovery Time	$t_{rr}$	$T_J = 150^\circ\text{C}$ , $I_{SD} = 2.2\text{A}$ , $dI_{SD}/dt = 100\text{A}/\mu\text{s}$		-	290	-	ns
Reverse Recovered Charge	$Q_{RR}$	$T_J = 150^\circ\text{C}$ , $I_{SD} = 2.2\text{A}$ , $dI_{SD}/dt = 100\text{A}/\mu\text{s}$		-	2.0	-	$\mu\text{C}$

#### NOTES:

- Pulse test: pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Repetitive rating: pulse width limited by max junction temperature. See Transient Thermal Impedance curve (Figure 3).
- $V_{DD} = 20\text{V}$ , start  $T_J = 25^\circ\text{C}$ ,  $L = 11.16\text{mH}$ ,  $R_G = 50\Omega$ , peak  $I_{AS}$ , 2.2A (Figures 14, 15).

### Typical Performance Curves

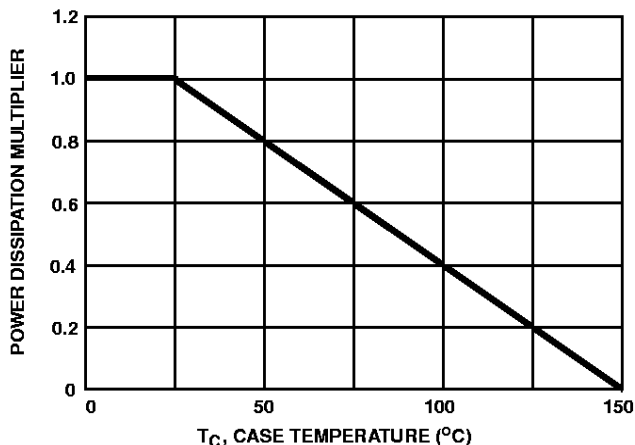


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

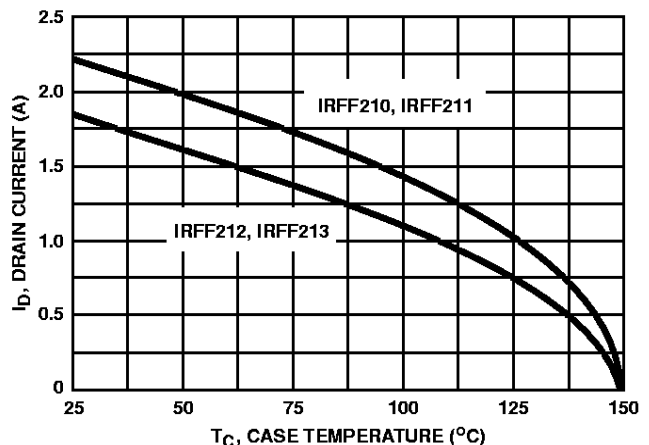


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

Typical Performance Curves (Continued)

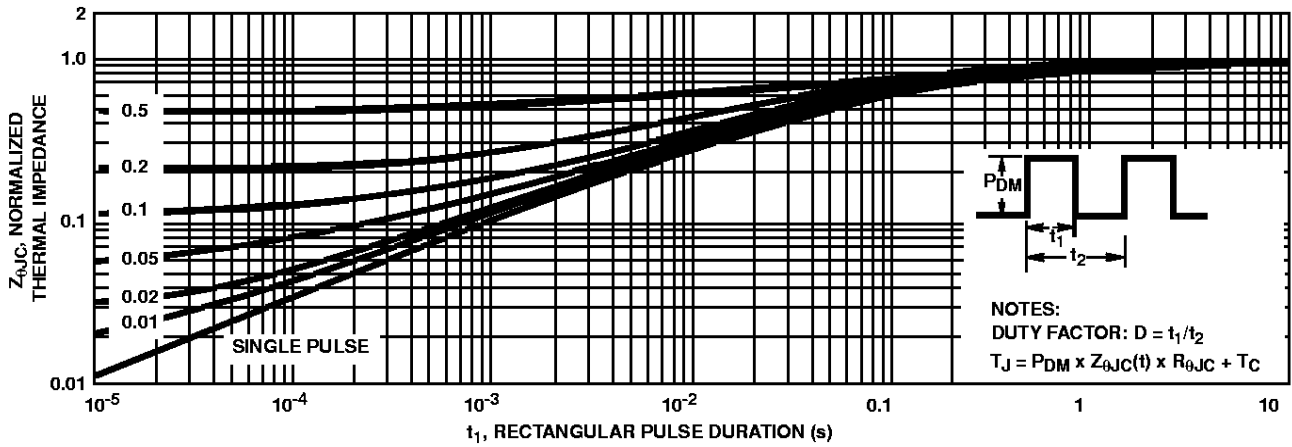


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

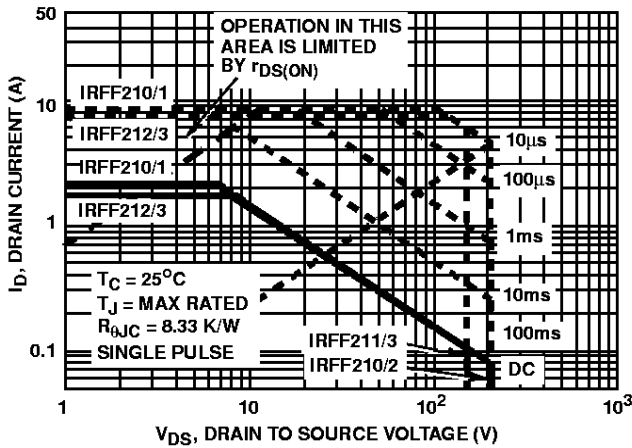


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

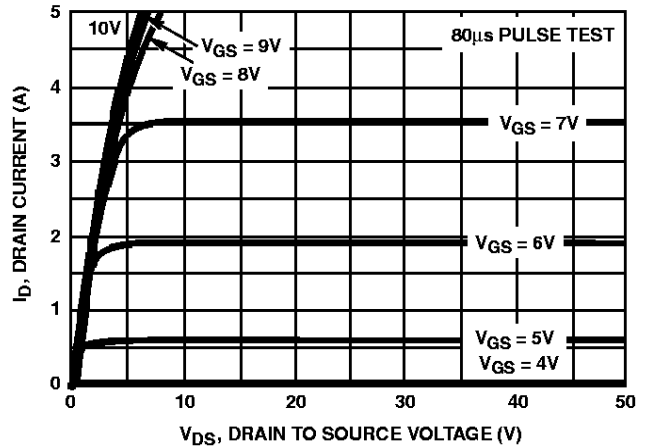


FIGURE 5. OUTPUT CHARACTERISTICS

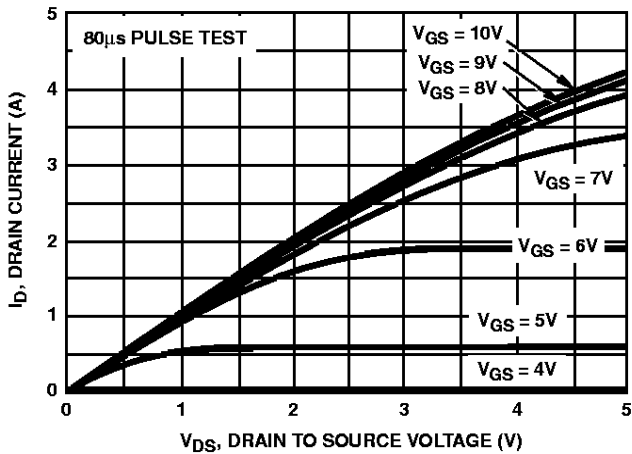


FIGURE 6. SATURATION CHARACTERISTICS

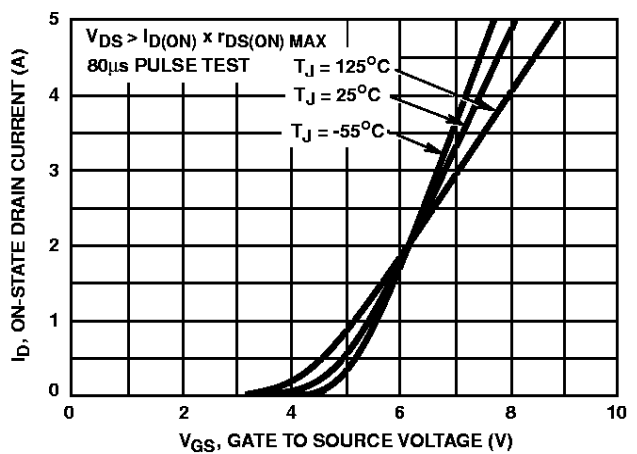


FIGURE 7. TRANSFER CHARACTERISTICS

Typical Performance Curves (Continued)

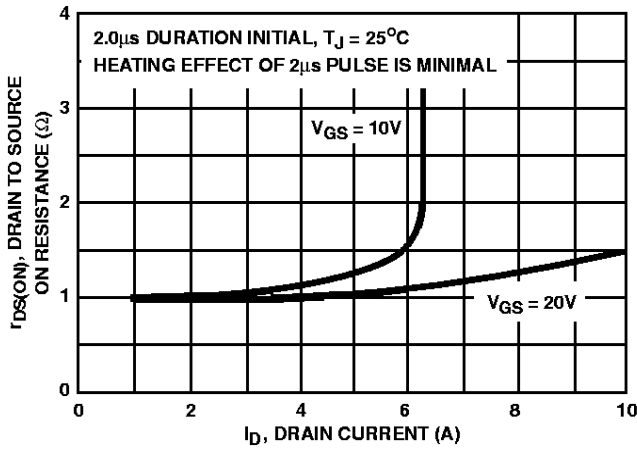


FIGURE 8. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

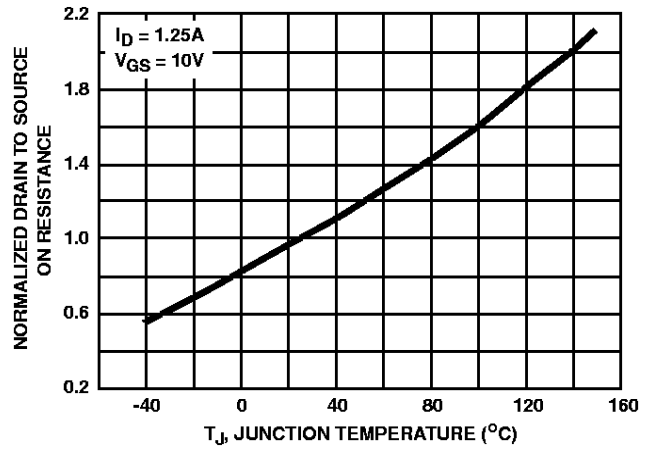


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

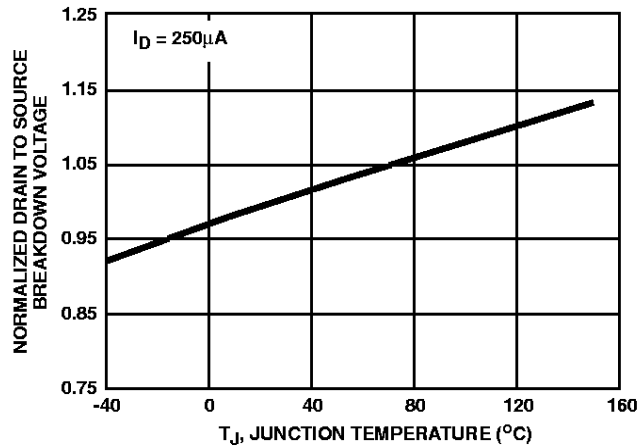


FIGURE 10. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

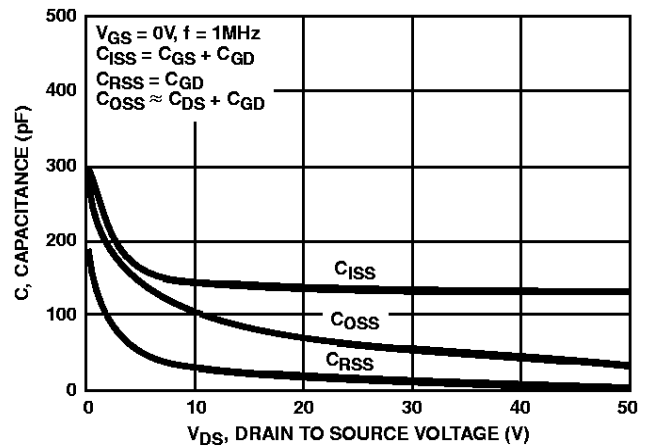


FIGURE 11. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

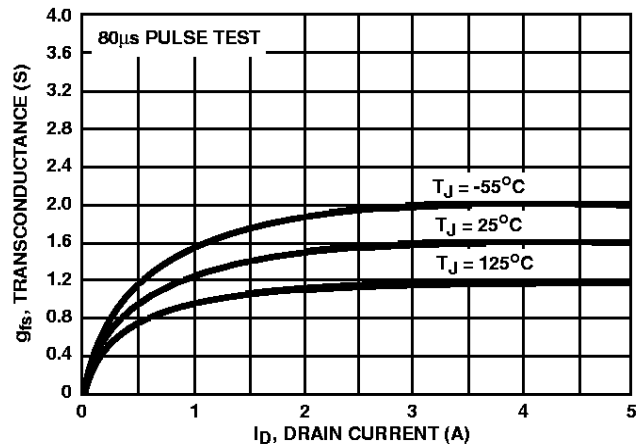


FIGURE 12. TRANSCONDUCTANCE vs DRAIN CURRENT

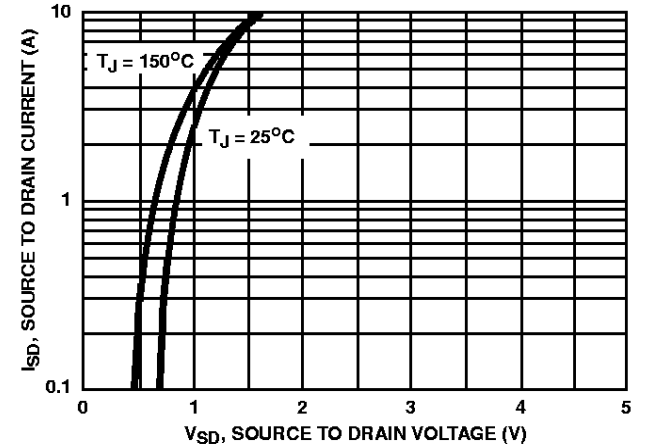


FIGURE 13. SOURCE TO DRAIN DIODE VOLTAGE

Typical Performance Curves (Continued)

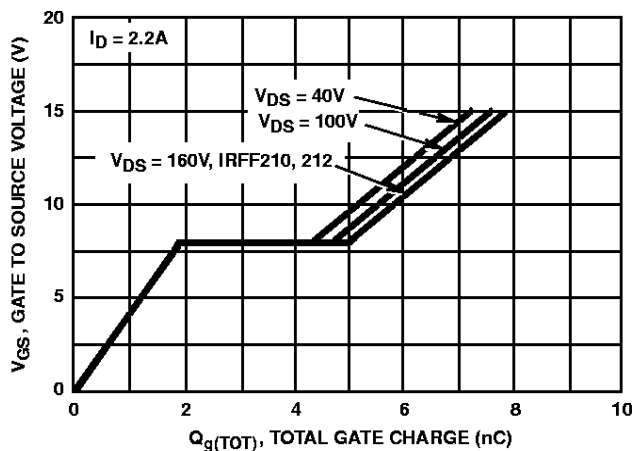


FIGURE 14. GATE TO SOURCE VOLTAGE vs GATE CHARGE

Test Circuits and Waveforms

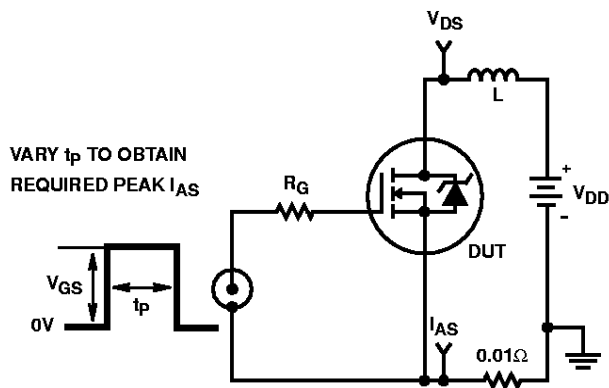


FIGURE 15. UNCLAMPED ENERGY TEST CIRCUIT

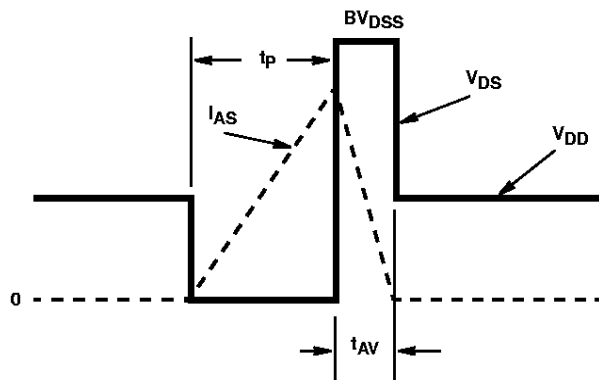


FIGURE 16. UNCLAMPED ENERGY WAVEFORMS

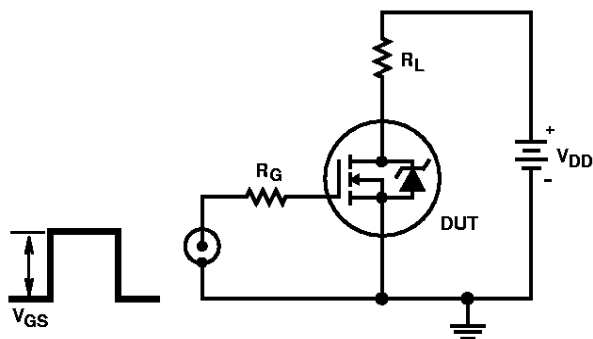


FIGURE 17. SWITCHING TIME TEST CIRCUIT

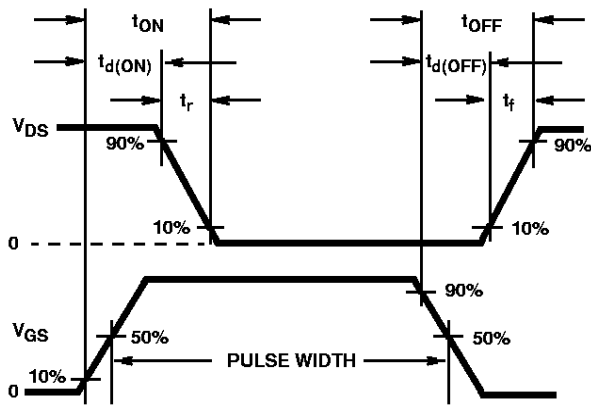


FIGURE 18. RESISTIVE SWITCHING WAVEFORMS

Test Circuits and Waveforms (Continued)

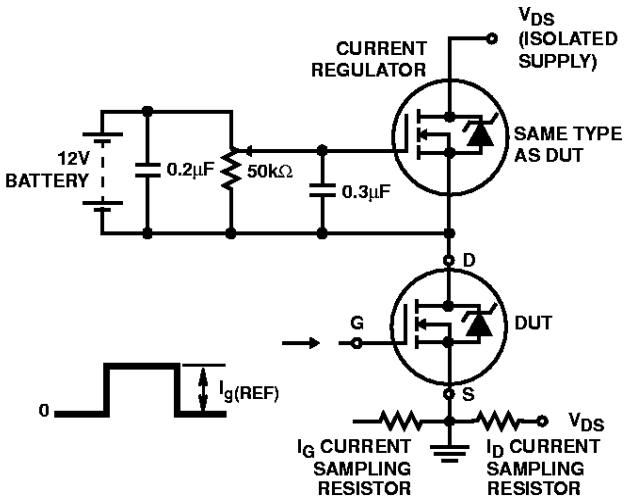


FIGURE 19. GATE CHARGE TEST CIRCUIT

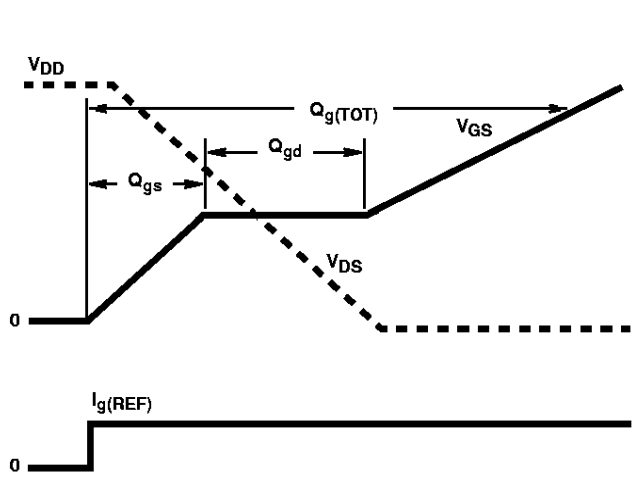


FIGURE 20. GATE CHARGE WAVEFORMS